1 Characteristics

Table 2. Absolute maximum ratings (limiting values; $T_j = 25$ °C, unless otherwise specified)

Symbol	Parameter				Unit	
I _{T(RMS)}	On-state rms current (full sine wave)		T _c = 88 °C	12	А	
I	Non repetitive surge peak on-state current (full	F = 50 Hz	t _p = 20 ms	90	٨	
	cycle, T _j initial = 25 °C)	F = 60 Hz	t _p = 16.7 ms	95	A	
l ² t	I^2 t Value for fusing $t_p = 10 \text{ ms}$			54	A ² s	
dl/dt	$ \begin{array}{ c c c } Critical rate of rise of on-state current I_G = 2 \times I_{GT} \\ t_r \leq 100 \text{ ns} \end{array} \hspace{0.2cm} F = 60 \text{ Hz} \hspace{0.2cm} T_j = 125 \ ^{\circ}\text{C} \\ \end{array} $		50	A/µs		
V _{DSM} , V _{RSM}	Non repetitive surge peak off-state $t_p = 10 \text{ ms}$ $T_j = 25 \text{ °C}$		V _{DRM} , V _{RRM} + 100	V		
I _{GM}	Peak gate current $t_p = 20 \ \mu s$ $T_j = 125 \ ^{\circ}C$		4	А		
P _{G(AV)}	Average gate power dissipation	1	W			
T _{stg}	Storage junction temperature range	- 40 to + 150	°C			
Тj	Operating junction temperature range			- 40 to + 125	°C	



Symbol	Test conditions	Quedrant		T12xxT			Unit	
	Test conditions	Quadrant		T1210T	T1220T	T1225T	T1235T	Unit
I _{GT} ⁽¹⁾	V 12V B 20.0	- -	MAX.	10	20	25	35	mA
IGT ` ′	$V_D = 12 V R_L = 30 \Omega$	IV				40		
V _{GT}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega,$ $T_j = 25 \text{ °C}$	ALL	MAX.	1.3				V
V _{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega,$ $T_j = 125 \text{ °C}$	ALL	MIN.	0.2				V
I _H ⁽²⁾	I _T = 500 mA	1	MAX.	10	15	20	30	mA
	I _G = 1.2 I _{GT}	I - III	MAX.	20	35	40	50	mA
ΙL		IV				40		
		II		30	40	60	80	
dV/dt ⁽²⁾	N 070/ N	T _j = 125 °C	MIN.	100	1000	100	2000	V/µs
av/at (/	$V_D = 67\% V_{DRM,}$ gate open	$T_j = 150 \ ^{\circ}C^{(3)}$		50	500	50	1000	
	(dV/dt)c = 0.1 V/µs			7		7		
	(dV/dt)c = 10 V/µs	T _j = 125 °C		3		3		
(-11/-10) - (2)	Without snubber		MINI		6		12	۸/ma
(dl/dt)c ⁽²⁾	(dV/dt)c = 0.1 V/µs		MIN.	3		3		A/ms
	(dV/dt)c = 10 V/µs	T _j = 150 °C ⁽³⁾		1		1		
	Without snubber	1			3		10	

Table 3. Electrical characteristics (T_i = 25 °C, unless otherwise specified)

1. Minimum $I_{\mbox{GT}}$ is guaranteed at 5% of $I_{\mbox{GT}}$ max.

2. For both polarities of A2 referenced to A1.

3. Derating information for excess temperature above ${\sf T}_j\,{\sf max}.$

Table 4. Static characteristics

Symbol	Test conditions	Value	Unit			
V _T ⁽¹⁾	I _{TM} = 17 A, t _p = 380 μs	T _j = 25 °C	MAX.	1.55	V	
V _{TO} ⁽¹⁾	Threshold voltage	T _j = 125 °C	MAX.	0.85	V	
$R_{D}^{(1)}$	Dynamic resistance	T _j = 125 °C	MAX.	35	mΩ	
_		T _j = 25 °C	MAX.	5	μA	
I _{DRM} I _{RRM}	V _{DRM} = V _{RRM}	T _j = 125 °C		1		
	$V_{D} = 0.9 \times V_{DRM}$	$T_j = 150 \ ^{\circ}C^{(2)}$	TYP.	1.9	mA	

1. For both polarities of A2 referenced to A1.

2. Derating information for excess temperature above ${\sf T}_j\,{\sf max}.$



	Table 5. Thermal resistance						
Symbol	Parameter	Value	Unit				
R _{th(j-c)}	Junction to case (AC)	2.6	°C/W				
R _{th(j-a)}	Junction to ambient (DC)	60	°C/W				

Figure 1. Maximum power dissipation versus rms on-state current (full cycle)

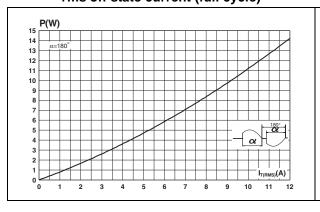


Figure 3. On-state rms current versus ambient temperature

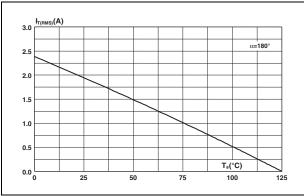


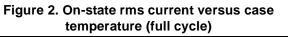
Figure 5. On state characteristics (maximum values)

100 I_{TM} (A)

10

1 ^L 0

4/8



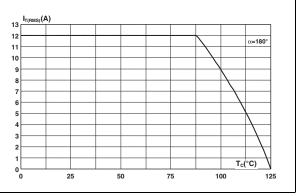


Figure 4. Relative variation of thermal impedance versus pulse duration

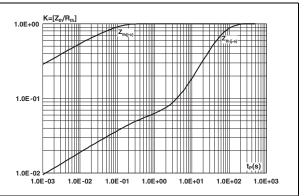
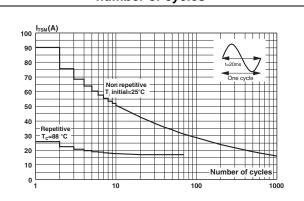


Figure 6. Surge peak on state current versus number of cycles



 $T_j max :$ $V_{to} = 0.85 V$ $R_d = 35 m\Omega$

1

5



Figure 7. Non repetitive surge peak on state current for a sinusoidal

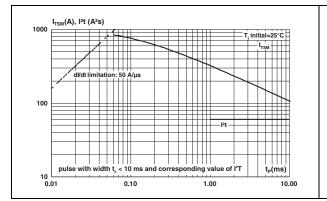


Figure 9. Relative variation of holding current and latching current versus junction temperature

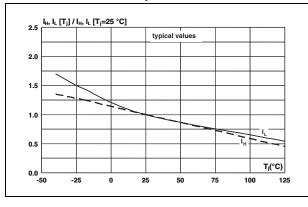
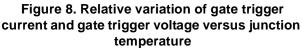


Figure 11. Relative variation of critical rate of decrease of main current versus junction temperature



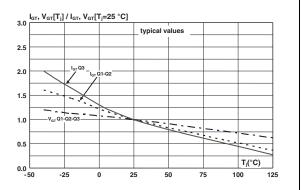


Figure 10. Relative variation of critical rate of decrease of main current versus (dV/dt)c

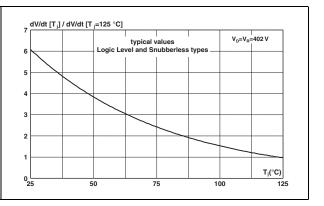
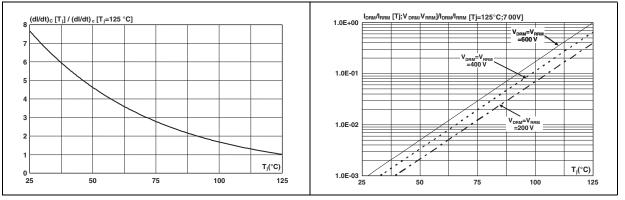


Figure 12. Leakage current versus junction temperature for different values of blocking voltage (typical values)





2 Package information

- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK[®] is an ST trademark.

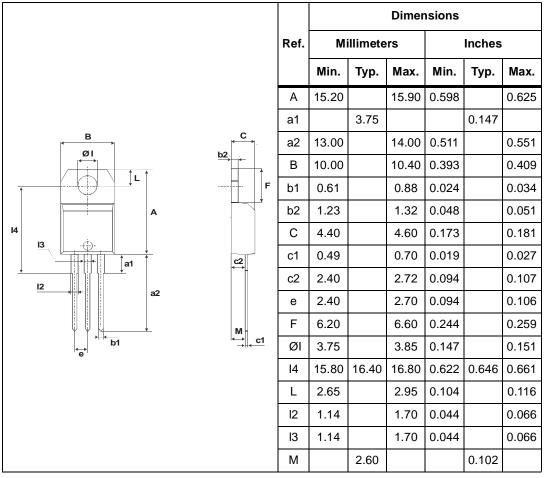


Table 6. TO-220AB insulated dimensions



3 Ordering information

5	er der nig n		0					
Triac		Ţ	12	10	T 	-	6	
Current								
12 = 12 A								
Sensitivity								
10 = 10 mA								
20 = 20 mA								
25 = 25 mA								
35 = 35 mA								
Application specific								
Voltage								
6 = 600 V								
Package								
I = TO-220AB-Ins.								

Figure 13. Ordering information scheme

 Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T1210T-6I	T1210T-6I				
T1220T-6I	T1220T-6I	TO-220AB-ins.	0.0 m	50	Tube
T1225T-6I	T1225T-6I	10-220AB-1115.	2.3 g	50	Tube
T1235T-6I	T1235T-6I				

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
03-Dec-2009	1	Initial release.
18-Jan-2010	2	Updated pag.1.
16-Sep-2013	3	Updated: <i>Features</i> . Replaced order codes with part numbers in <i>Table 1</i> .



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